

Qi Wang

List of Publications by Year in descending order

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#	ARTICLE	IF	CITATIONS
1	Facile fabrication of wafer-scale flexible SERS substrate via cryo-transferring SiO ₂ nanosphere multilayer into waterborne polyurethane (WPU) film. <i>Materials Letters</i> , 2022, 317, 132063.	1.3	1
2	A robust, flexible adhesive tape-based SERS substrate fabricated by polymer etching and subsequent Au coating on the exposed SiO ₂ nanosphere monolayer. <i>Spectrochimica Acta - Part A: Molecular and Biomolecular Spectroscopy</i> , 2022, 281, 121626.	2.0	4
3	Facile fabrication of Au nanoworms covered polyethylene terephthalate (PET) film: Towards flexible SERS substrates. <i>Materials Letters</i> , 2021, 294, 129643.	1.3	8
4	Rolled-up InGaAs/GaAs/RGO trilayer microtubes: Fabrication, characterizations and rolling behaviors. <i>Materials Science in Semiconductor Processing</i> , 2020, 105, 104696.	1.9	0
5	Highly stretchable and sensitive liquid-type strain sensor based on a porous elastic rope/elastomer matrix composite structure. <i>Composites Science and Technology</i> , 2019, 182, 107707.	3.8	12
6	Tracing the Motion of Finger Joints for Gesture Recognition via Sewing RGO-Coated Fibers Onto a Textile Glove. <i>IEEE Sensors Journal</i> , 2019, 19, 9504-9511.	2.4	44
7	A flexible and skin-mountable elastic fiber-based sensor patch for healthcare monitoring. <i>Biomedical Physics and Engineering Express</i> , 2019, 5, 045011.	0.6	9
8	Experiment on VCSEL Composed of Special Structure DBRs in Integrated Optoelectronic Chip. <i>IEEE Access</i> , 2019, 7, 175622-175627.	2.6	1
9	Multifunctional devices based on SnO ₂ @rGO-coated fibers for human motion monitoring, ethanol detection, and photo response. <i>Nanotechnology</i> , 2018, 29, 195501.	1.3	11
10	Optically pumped lasing in a rolled-up dot-in-a-well (DWELL) microtube via the support of Au pad. <i>Applied Physics B: Lasers and Optics</i> , 2018, 124, 1.	1.1	5
11	Periodic silver nanocluster arrays over large-area silica nanosphere template as highly sensitive SERS substrate. <i>Applied Surface Science</i> , 2018, 437, 92-97.	3.1	47
12	Room temperature observation of optical modes in transferred rolled-up InGaAs/GaAs quantum dot microtube with AlGaAs confining layers. <i>Materials Science in Semiconductor Processing</i> , 2018, 79, 20-23.	1.9	4
13	Human motion monitoring in sports using wearable graphene-coated fiber sensors. <i>Sensors and Actuators A: Physical</i> , 2018, 274, 132-140.	2.0	73
14	RGO-coated elastic fibres as wearable strain sensors for full-scale detection of human motions. <i>Smart Materials and Structures</i> , 2018, 27, 015014.	1.8	25
15	1.3 μm whispering gallery modes observed in a Si-based rolled-up InAs/GaAs bilayer quantum dot (BQD) microtube at room-temperature. , 2018, , .		0
16	Sensitive Liquid Sensing Using Rolled-Up InAs/GaAs Quantum Dot Microtube Ring Resonator. , 2018, , .		1
17	Realization of uniaxially strained, rolled-up monolayer CVD graphene on a Si platform via heteroepitaxial InGaAs/GaAs bilayers. <i>RSC Advances</i> , 2017, 7, 14481-14486.	1.7	10
18	A facile, precise radial artery pulse sensor based on stretchable graphene-coated fiber. <i>Sensors and Actuators A: Physical</i> , 2017, 267, 532-537.	2.0	17

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19	A Wearable Motion Monitoring Fiber Sensor Based on Graphene. , 2017, , .		0
20	Fabrication and performance of In _{0.66} Ga _{0.34} As _{0.73} P _{0.27} /In _{0.89} Ga _{0.11} As _{0.23} P _{0.77} multiple-quantum-well lasers. , 2016, , .		0
21	MOCVD growth and characterization of multi-stacked InAs/GaAs quantum dots on misoriented Si(100) emitting near 1.3 μ m. Journal of Crystal Growth, 2016, 455, 168-171.	0.7	10
22	Graphite oxide-coated Au nanoparticles for improved SERS sensing. , 2016, , .		0
23	Gold nanoparticle-induced diameter reduction and enhanced Raman shift in self-rolled-up InGaAs/GaAs microtubes. , 2016, , .		0
24	Optical studies of free-standing GaAs/AlGaAs single quantum well (SQW) microtubes: A comparison with InGaAs/GaAs bilayer microtubes. Materials Letters, 2016, 166, 263-266.	1.3	3
25	Micro-photoluminescence and micro-Raman investigations of rolled-up InGaAs/GaAs microtubes monolithically integrated on silicon. Applied Physics Letters, 2015, 107, 082108.	1.5	7
26	Micro-Raman investigations of free-standing GaAs/AlGaAs single quantum well (SQW) microtubes. , 2015, , .		0
27	Extremely Low-Threshold Current Density InGaAs/AlGaAs Quantum-Well Lasers on Silicon. Journal of Lightwave Technology, 2015, 33, 3163-3169.	2.7	25
28	Coalescence of GaAs on (001) Si nano-trenches based on three-stage epitaxial lateral overgrowth. Applied Physics Letters, 2015, 106, .	1.5	21
29	DWELL based laser structure grown by LP-MOCVD using InGaP as p-doped cladding layer. , 2015, , .		1
30	Enhanced absorption of graphene strips with a multilayer subwavelength grating structure. Applied Physics Letters, 2014, 105, 221113.	1.5	57
31	Selective area growth of InP on lithography-free, nanopatterned GaAs(001) by metalorganic chemical vapor deposition. Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics, 2014, 32, 011210.	0.6	1
32	Self-rolled-up InGaAs/GaAs microtubes fabricated directly on Si (100) substrates. Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics, 2014, 32, 030603.	0.6	3
33	LP-MOCVD growth of BGaAsSb thick layers and BGaAsSb/GaAs quantum well structures on GaAs (001) substrates. Journal of Crystal Growth, 2014, 394, 74-80.	0.7	3
34	Effects of boron incorporation on the strain and photoluminescence properties of GaAsSb/GaAs quantum wells. Materials Science in Semiconductor Processing, 2013, 16, 1713-1717.	1.9	3
35	Effect of boron incorporation on the structural and photoluminescence properties of highly-strained In _x Ga _{1-x} As/GaAs multiple quantum wells. AIP Advances, 2013, 3, 072111.	0.6	7
36	The electronic and optical properties of quaternary B _x Ga _{1-x} As _{1-y} Sb _y alloys with low boron concentration: A first-principles study. Journal of Alloys and Compounds, 2013, 563, 18-21.	2.8	4

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37	Three-step growth of metamorphic GaAs on Si(001) by low-pressure metal organic chemical vapor deposition. Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics, 2013, 31, 051211.	0.6	24
38	Dependence of doubly curved regions on drying method in the fabrication of long-side rolled-up III-V microtubes. Applied Physics Letters, 2013, 103, 051909.	1.5	8
39	The LP-MOCVD growth of B GaAs alloys with different gallium precursors. , 2013, , .		0
40	First-principle study of the electronic and optical properties of BInGaAs quaternary alloy lattice-matched to GaAs. Physica B: Condensed Matter, 2012, 407, 4570-4573.	1.3	16
41	The saturation density property of (B)InAs/GaAs quantum dots grown by metal-organic chemical vapor deposition. Physica E: Low-Dimensional Systems and Nanostructures, 2012, 44, 1146-1151.	1.3	9
42	Selective etching of GaAs/Si and InP/GaAs heteroepitaxial wafer. , 2012, , .		0
43	The influence of growth parameters on the formation on InAs/GaAs by MOCVD. , 2012, , .		1
44	First-principle calculations of dilute nitride Ga _{1-x} N _x alloy in zinc-blende structures. Physica B: Condensed Matter, 2012, 407, 112-115.	1.3	4
45	Structural and optical characterization of highly-strained BInGaAs/GaAs quantum wells. , 2012, , .		0
46	MOCVD growth and characterizations of B _x Al _{1-x} As and B _x Al _{1-x} As _y In _y As alloys. Journal of Alloys and Compounds, 2011, 509, 5631-5636.	2.8	12
47	The influence of graded In _x Ga _{1-x} As on strain distribution and the band gap in the InAs/GaAs quantum dots. , 2011, , .		0
48	Effect of boron on the surface and optical properties for (B)InAs/GaAs self-assembled quantum dots grown by MOCVD. , 2011, , .		0
49	First-principles calculations of band-gap properties of zinc-blende B _x Ga _{1-x} N and B _x Ga _{1-x} N _y As _{1-y} alloys. Proceedings of SPIE, 2011, , .	0.8	0
50	The effect of growth temperature on InAs quantum dots grown by MOCVD. , 2011, , .		0
51	Numerical studies on flow and thermal fields in MOCVD reactor. Science Bulletin, 2010, 55, 560-566.	1.7	6
52	First-Principles Study of Fundamental Properties of B _x In _{1-x} P Alloys. , 2010, , .		0
53	First-Principles Study of Structural and Electronic Properties of Ga _x As _{1-x} Alloys. , 2010, , .		0
54	The band structures of BSb and B _x Ga _{1-x} Sb alloys. Science in China Series G: Physics, Mechanics and Astronomy, 2009, 52, 843-847.	0.2	8

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55	Growth of $B_xGa_{1-x}As$, $B_xAl_{1-x}As$ and $B_xGa_{1-x}As_yIn_yAs$ epilayers on (001)GaAs by low pressure metalorganic chemical vapor deposition. <i>Microelectronics Journal</i> , 2009, 40, 87-91.	1.1	30
56	LP-MOCVD growth of ternary $B_xGa_{1-x}As$ epilayers on (001)GaAs substrates using TEB, TMGa and AsH ₃ . <i>Microelectronics Journal</i> , 2008, 39, 1678-1682.	1.1	18
57	Growth of $B_xGa_{1-x}As$, $B_xAl_{1-x}As$ and $B_xGa_{1-x}As_yIn_yAs$ epilayers on (001)GaAs by LP-MOCVD. <i>Proceedings of SPIE</i> , 2008, , .	0.8	0
58	Analysis and simulation of process parameters for epitaxy of InP-based compound semiconductor materials. <i>Proceedings of SPIE</i> , 2008, , .	0.8	1
59	Buffer optimization for high-quality InP-on-GaAs(001) quasi-substrates. , 2007, , .		0
60	Epitaxial lateral overgrowth of InP/GaAs (100) heterostructures by metalorganic chemical vapor deposition. <i>Microelectronics Journal</i> , 2007, 38, 606-609.	1.1	2
61	<title>Investigation of InP epitaxial films on GaAs substrate grown by LP-MOCVD</title>. , 2006, 6029, 190.		0
62	Heteroepitaxy of In _{0.53} Ga _{0.47} As on GaAs substrate by low pressure metalorganic chemical vapor deposition for the OEIC applications. <i>Microelectronics Journal</i> , 2006, 37, 700-704.	1.1	9